

BTA201W series E

1 A Three-quadrant triacs high commutation Rev. 02 — 17 September 2007

Product data sheet

Product profile

1.1 General description

Passivated guaranteed commutation triacs in a surface-mounted plastic package, intended for interfacing with low-power drivers, including microcontrollers.

1.2 Features

- Suitable for interfacing with low-power drivers, including microcontrollers
- SOT223 surface mounted

1.3 Applications

Motor control

Solenoid drivers

1.4 Quick reference data

- $\blacksquare \quad I_{TSM} \leq 12.5 \text{ A}$
- V_{DRM} ≤ 600 V (BTA201W-600E)
- $V_{DRM} \le 800 \text{ V (BTA201W-800E)}$
- $I_{T(RMS)} \le 1 A$
- I_{GT} ≤ 10 mA

Pinning information

Table 1. **Pinning**

	3		
Pin	Description	Simplified outline	Symbol
1	main terminal 1 (T1)		
2	main terminal 2 (T2)	4	T2—T1
3	gate (G)		sym051
4	main terminal 2 (T2)	1 2 3	
		SOT223	



3. Ordering information

Table 2. Ordering information

Type number	Package				
	Name	Description	Version		
BTA201W-600E	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		
BTA201W-800E					

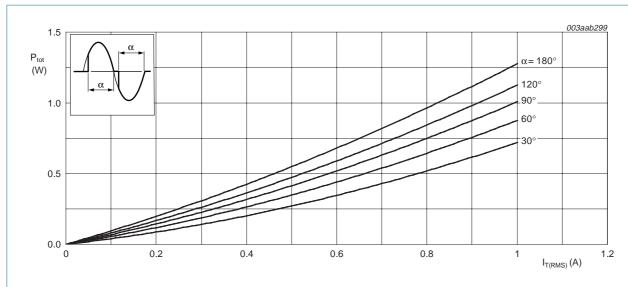
4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

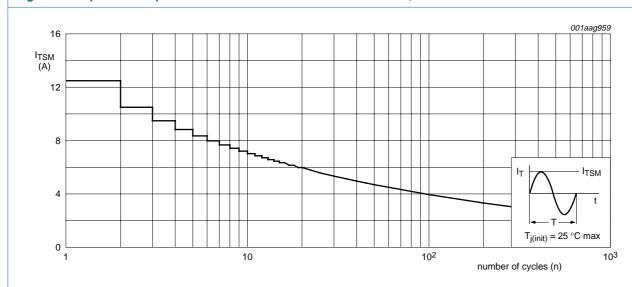
Parameter	Conditions		Min	Max	Unit
repetitive peak off-state voltage	BTA201W-600E	<u>[1]</u>	-	600	V
	BTA201W-800E		-	800	V
RMS on-state current	full sine wave; $T_{sp} \le 106$ °C; see Figure 4 and 5		-	1	Α
non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3				
	t = 20 ms		-	12.5	Α
	t = 16.7 ms	- - -	-	13.7	Α
I ² t for fusing	t = 10 ms		-	0.78	A ² s
rate of rise of on-state current	$I_{TM} = 1.5 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$		-	100	A/μs
peak gate current			-	2	Α
peak gate power			-	5	W
average gate power	over any 20 ms period		-	0.1	W
storage temperature			-40	+150	°C
junction temperature			-	125	°C
	repetitive peak off-state voltage RMS on-state current non-repetitive peak on-state current I²t for fusing rate of rise of on-state current peak gate current peak gate power average gate power storage temperature	repetitive peak off-state voltage $BTA201W-600E$ $BTA201W-800E$ $RMS \ on\text{-state current} \qquad \text{full sine wave; $T_{sp} \le 106 °C$; $see \ \hline{Figure 4}$ and 5}$ $non\text{-repetitive peak on-state current} \qquad \text{full sine wave; $T_j = 25 °C$ prior to surge; $see \ \hline{Figure 2}$ and 3}$ $t = 20 \ ms$ $t = 16.7 \ ms$ $l^2t \ for \ fusing \qquad t = 10 \ ms$ $rate \ of \ rise \ of \ on\text{-state current} \qquad l_{TM} = 1.5 \ A; \ l_G = 0.2 \ A; \\ dl_G/dt = 0.2 \ A/\mu s$ $peak \ gate \ current$ $peak \ gate \ power$ $average \ gate \ power$ $average \ gate \ power$ $over \ any \ 20 \ ms \ period$ $storage \ temperature$		repetitive peak off-state voltage	repetitive peak off-state voltage $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

^[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/μs.



 α = conduction angle

Fig 1. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

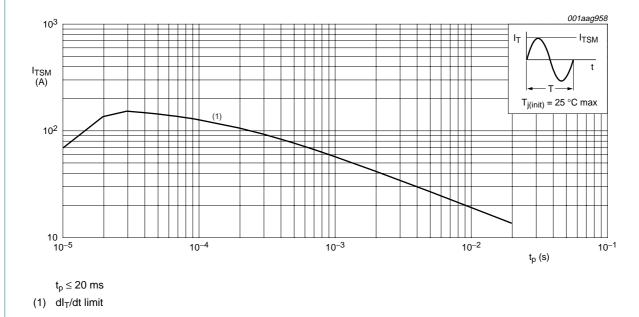


Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values

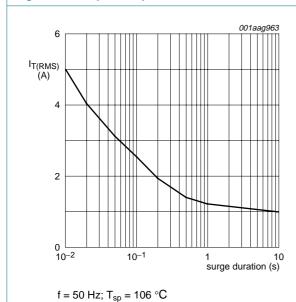


Fig 4. RMS on-state current as a function of surge duration; maximum values

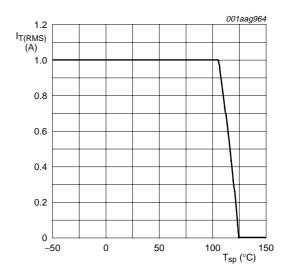


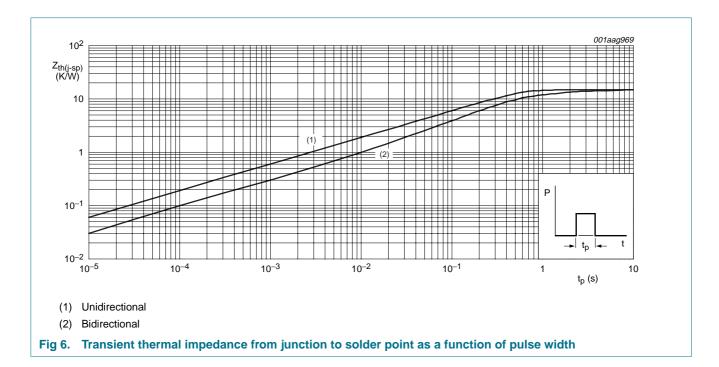
Fig 5. RMS on-state current as a function of solder point temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	see Figure 6	-	-	15	K/W
uily a)	thermal resistance from	minimum footprint; see Figure 14	<u>[1]</u> -	156	-	K/W
	junction to ambient	for pad area; see Figure 15	<u>[1]</u> -	70	-	K/W

[1] Mounted on a printed-circuit board.



6. Static characteristics

Table 5. Static characteristics

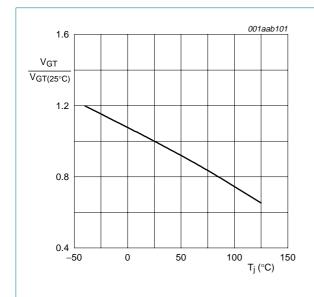
 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BTA201W-	600E and BTA201W-800E					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ see } \frac{\text{Figure 8}}{}$				
		T2+ G+	-	-	10	mA
		T2+ G-	-	-	10	mA
		T2- G-	-	-	10	mA
I _L latching curre	latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 10}{\text{M}}$				
		T2+ G+	-	-	12	mA
		T2+ G-	-	-	20	mA
		T2- G-	-	-	12	mA
I _H	holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 11}{\text{Model}}$	-	-	12	mA
V _T	on-state voltage	I _T = 1.4 A; see <u>Figure 9</u>	-	1.2	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ see } \frac{\text{Figure 7}}{}$	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C}$	0.2	0.3	-	V
I _D	off-state current	$V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$	-	0.1	0.5	mA

7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BTA201W	-600E and BTA201W-800	E				
dV _D /dt	rate of rise of off-state voltage	$V_{DM} = 0.67 V_{DRM(max)}$; $T_j = 125 ^{\circ}C$; exponential waveform; gate open circuit	600	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	V_{DM} = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 4 A; gate open circuit				
		$dV_{com}/dt = 20 V/\mu s$	2.5	-	-	A/ms
		$dV_{com}/dt = 10 V/\mu s$	3.5	-	-	A/ms
t _{gt}	gate-controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



3 003aaa959

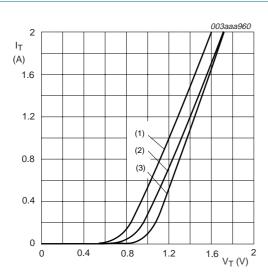
IGT
IGT(25°C)
2 (1)
(2)
(3)
(3)
(2)
(1)
0 -50 0 50 100 T_j (°C) 150

- (1) T2-G-
- (2) T2+ G-
- (3) T2+ G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature

Fig 8. Normalized gate trigger current as a function of junction temperature

BTA201W_SER_E_2 © NXP B.V. 2007. All rights reserved.



 $V_0 = 1.02 \text{ V}; R_s = 358 \text{ m}\Omega$

- (1) $T_j = 125 \,^{\circ}C$; typical values
- (2) T_i = 125 °C; maximum values
- (3) $T_j = 25 \,^{\circ}C$; maximum values

Fig 9. On-state current as a function of on-state voltage

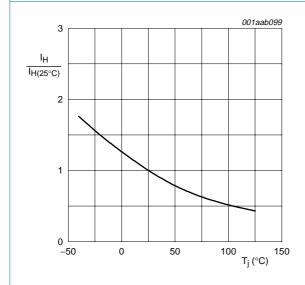


Fig 11. Normalized holding current as a function of junction temperature

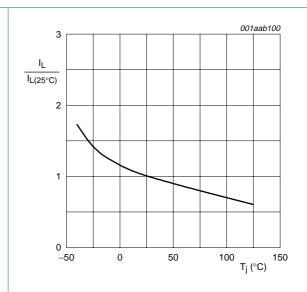
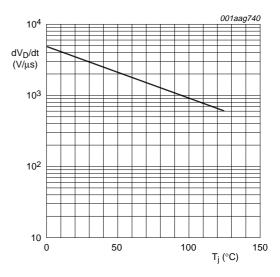


Fig 10. Normalized latching current as a function of junction temperature



Gate open circuit

Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

BTA201W_SER_E_2 © NXP B.V. 2007. All rights reserved.

8. Package outline

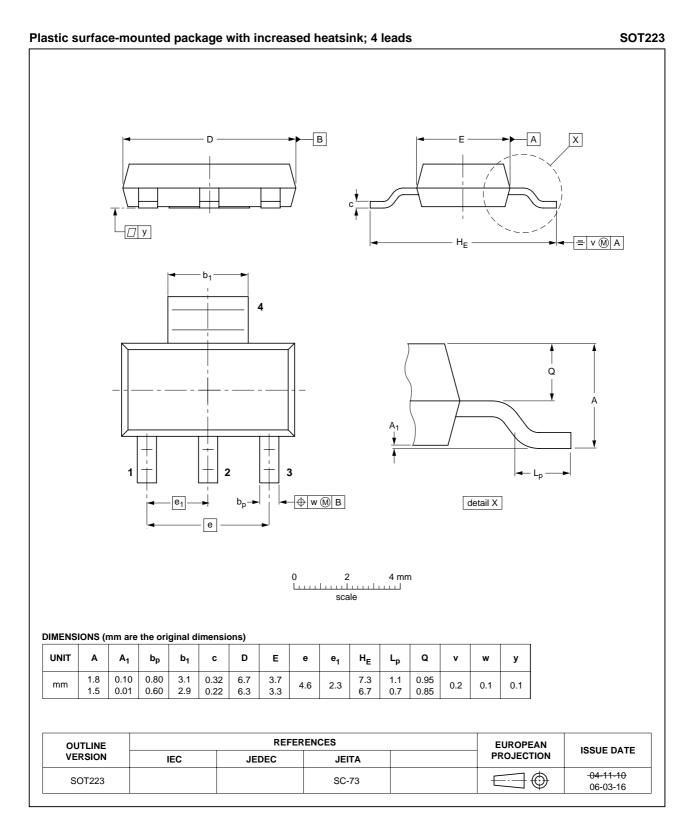
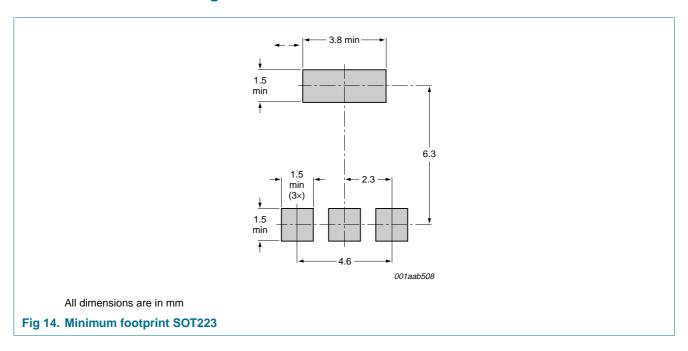


Fig 13. Package outline SOT223

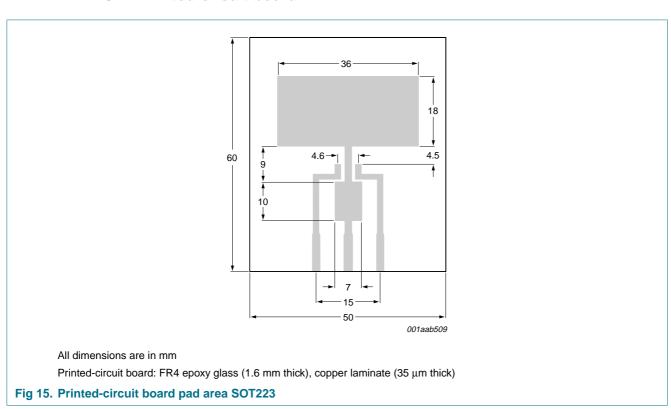
BTA201W_SER_E_2 © NXP B.V. 2007. All rights reserved.

9. Mounting

9.1 Mounting instructions



9.2 Printed-circuit board



10. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA201W_SER_E_2	20070917	Product data sheet	-	BTA201W_SER_E_1
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity
	 Legal texts 	have been adapted to the n	ew company name whe	ere appropriate.
	 Descriptive 	titles have been corrected.		
	 Table 3 "Lim 	niting values" on page 2: dl _T	dt uprated	
	 Table 6 "Dyl 	namic characteristics" on pa	age 7: dV _D /dt uprated	
		Critical rate of rise of off-state llues" on page 8: graph upd		of junction temperature;
BTA201W_SER_E_1	20060207	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

11.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

11.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or

malfunction of a NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

11.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

12. Contact information

For additional information, please visit: http://www.nxp.com

For sales office addresses, send an email to: salesaddresses@nxp.com

BTA201W series E

1 A Three-quadrant triacs high commutation

13. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
1.4	Quick reference data
2	Pinning information 1
3	Ordering information
4	Limiting values
5	Thermal characteristics 5
6	Static characteristics 6
7	Dynamic characteristics
8	Package outline 9
9	Mounting
9.1	Mounting instructions
9.2	Printed-circuit board
10	Revision history
11	Legal information
11.1	Data sheet status
11.2	Definitions
11.3	Disclaimers
11.4	Trademarks 12
12	Contact information
13	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

